



Diagram illustrating a cross-sectional view of a semiconductor device. The structure shows a substrate (P-TYPE WELL) with a well (5) and a gate stack (1, 2, 3, 4) on top. The gate stack consists of layers 1, 2, 3, and 4. The substrate is labeled 6 and 7.

Fig.20 PRIOR ART

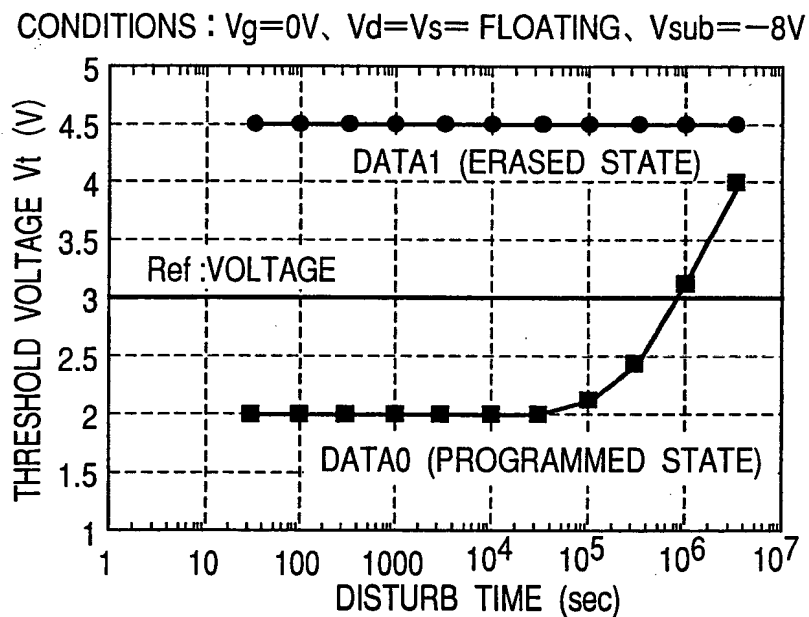
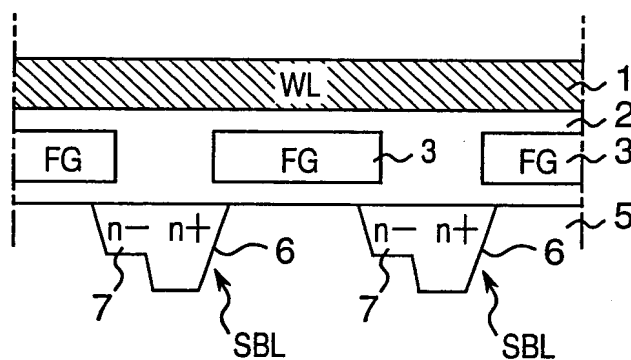




Fig.21 PRIOR ART



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